WNSC6D16650CW



Silicon Carbide Diode Rev.01 - 25 January 2022

Product data sheet

1. General description

Silicon Carbide Schottky diode in a TO247-3L plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- New 6th Generation Technology
- Low Forward Voltage Drop
- Low Reverse Leakage Current
- High Forward Surge Capability I_{FSM}
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

| Table 1. Q | uick reference data | | | | | |
|------------------|---------------------------------|---|--------|------|------|------|
| Symbol | Parameter | Conditions | Values | | | Unit |
| Absolute | maximum rating | | | | | |
| V_{RRM} | repetitive peak reverse voltage | | 650 | | | V |
| $I_{F(AV)}$ | average forward current | δ = 0.5 ; square-wave pulse; T _{mb} ≤ 142 °C; Fig. 1; Fig. 2; Fig. 3 | 16 | | A | |
| Tj | junction temperature | | 175 | | °C | |
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static ch | aracteristics | · | | | | |
| V _F | forward voltage | I _F = 16 A; T _j = 25 °C; <u>Fig. 5</u> | - | 1.29 | 1.45 | V |
| | | I _F = 16 A; T _j = 150 °C; <u>Fig. 5</u> | - | 1.45 | 1.65 | V |
| Dynamic | characteristics | | | | | |
| Q _r | recovered charge | $I_F = 16 \text{ A}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s}; \text{ V}_R = 400 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$ | - | 36 | - | nC |

5. Pinning information

| Table 2. Pinning information | | | | | | | |
|------------------------------|--------|-------------------------------------|--------------------|----------------|--|--|--|
| Pin | Symbol | Description | Simplified outline | Graphic symbol | | | |
| 1 | А | anode | | к_Ң_А | | | |
| 2 | К | cathode | | 001aaa020 | | | |
| 3 | А | anode | | | | | |
| mb | К | mounting base; connected to cathode | | | | | |

6. Ordering information

| Table 3. Ordering information | | | | | | | |
|-------------------------------|-----------------|-----------------------|-------------------|---------------------------|-----------------|--------------------|--|
| Type number | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date | |
| WNSC6D16650CW | TO247 | WNSC6D16650CW6Q | Tube | 30 | SOT429 | 25-Mar-2013 | |

7. Marking

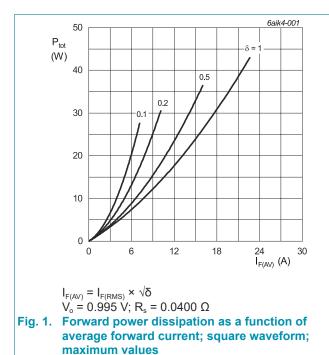
| Table 4. Marking codes | | | | | | |
|------------------------|-------------------|--|--|--|--|--|
| Type number | Marking codes | | | | | |
| WNSC6D16650CW | WNSC6D 16650CW | | | | | |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Values | Unit |
|------------------|---------------------------------|---|------------|------------------|
| V_{RRM} | repetitive peak reverse voltage | | 650 | V |
| V_{RWM} | crest working reverse voltage | | 650 | V |
| V _R | reverse voltage | DC | 650 | V |
| $I_{F(AV)}$ | average forward current | δ = 0.5; square-wave pulse; T _{mb} ≤ 142 °C; Fig. 1; Fig. 2; Fig. 3 | 16 | A |
| I _{FRM} | repetitive peak forward current | δ = 0.5; t _p = 25 µs; T _{mb} ≤ 142 °C; square-wave pulse | 32 | A |
| I _{FSM} | non-repetitive peak | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | 110 | А |
| | forward current | t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse | 900 | А |
| l ² t | I ² t for fusing | sine-wave pulse; $T_{j(init)}$ = 25 °C; t_p = 10 ms | 61 | A ² s |
| T _{stg} | storage temperature | | -55 to 175 | °C |
| T _j | junction temperature | | 175 | °C |



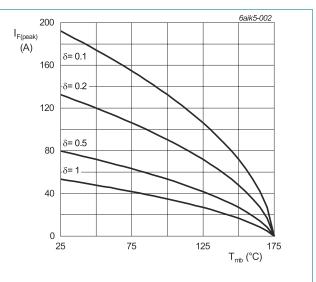
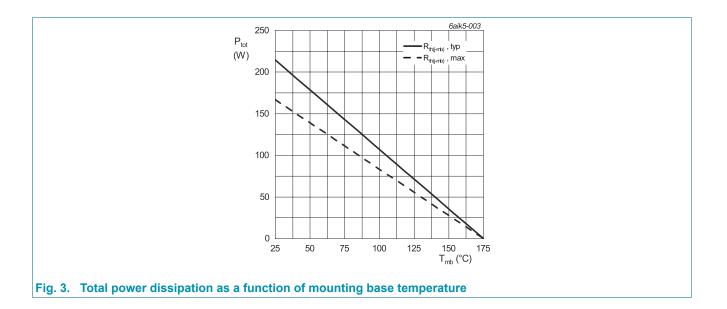
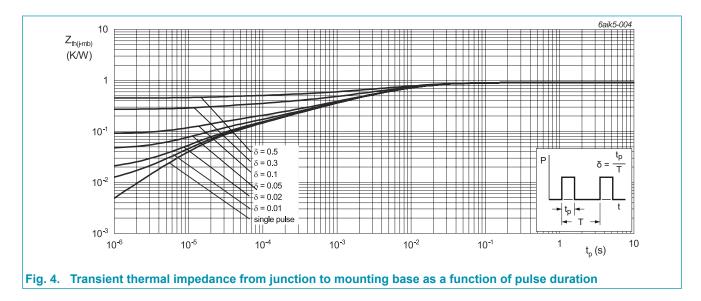


Fig. 2. Current derating as a function of mounting base temperature

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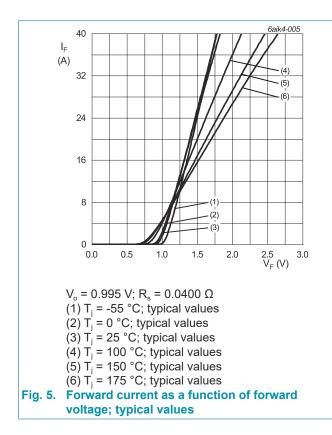


| Table 6. Thermal characteristics | | | | | | | | |
|----------------------------------|--|-------------|--|-----|-----|-----|------|--|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit | |
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 4 | | - | 0.7 | 0.9 | K/W | |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient free air | in free air | | - | 40 | - | K/W | |



10. Characteristics

| able 7. C | haracteristics | | | | | |
|-----------------|------------------------------------|---|-----|------|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | aracteristics | | | | | |
| V _F | forward current | I _F = 16 A; T _j = 25 °C; <u>Fig. 5</u> | - | 1.29 | 1.45 | V |
| | | I _F = 16 A; T _j = 150 °C; <u>Fig. 5</u> | - | 1.45 | 1.65 | V |
| | | I _F = 16 A; T _j = 175 °C; <u>Fig. 5</u> | - | 1.50 | 1.7 | V |
| I _R | reverse current | V _R = 650 V; T _j = 25 °C; <u>Fig. 6</u> | - | 1 | 80 | μA |
| | | V _R = 650 V; T _j = 175 °C; <u>Fig. 6</u> | - | 25 | 320 | μA |
| Dynamic | characteristics | · · · · · · | | | | |
| Q _r | recovered charge | $I_F = 16 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$ | - | 36 | - | nC |
| C _d | diode capacitance | f = 1 MHz; V _R = 1 V; T _j = 25 °C | - | 780 | - | pF |
| | | f = 1 MHz; V _R = 300 V; T _j = 25 °C | - | 86 | - | pF |
| | | f = 1 MHz; V _R = 600 V; T _j = 25 °C | - | 79 | - | pF |
| E _{as} | non-repetitive avalanche energy | I _R = 7 A; L = 5 mH; T _{j(init)} = 25 °C | 120 | - | - | mJ |



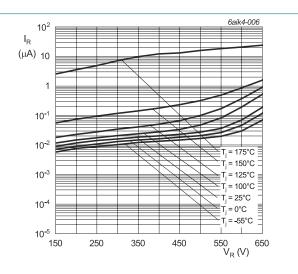
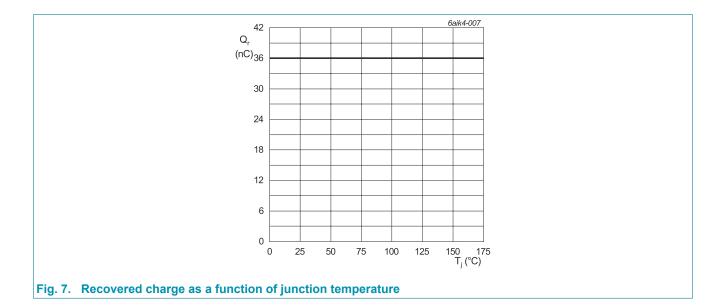


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value

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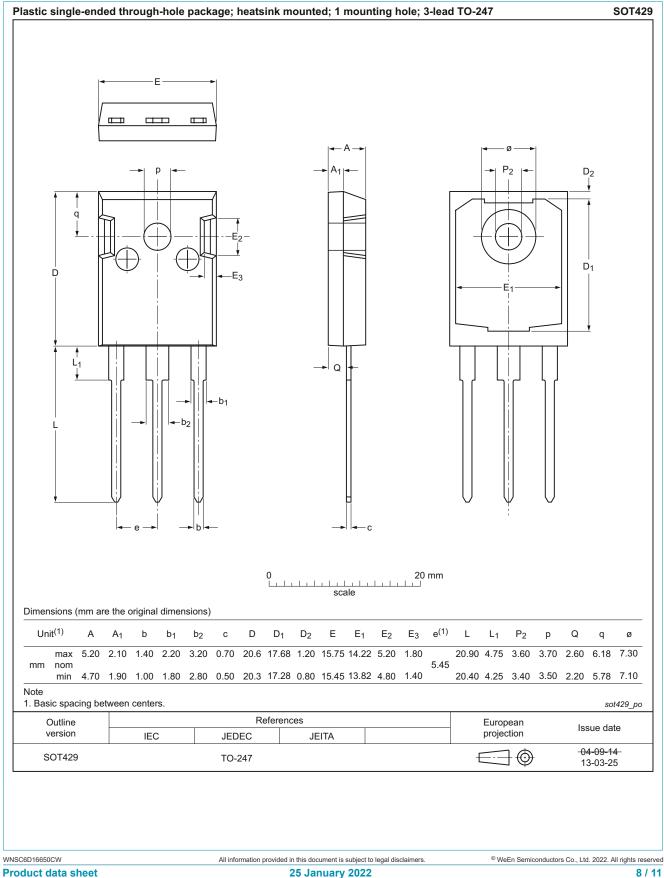
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11. Package outline



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12. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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- [2] The term 'short data sheet' is explained in section "Definitions".
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